NGSF3443V

Preferred Device

Advance Information

Low $r_{DS(on)}$ TMOS Single P-Channel Field Effect Transistors

MiniMOS devices are designed for use in low voltage, high speed switching applications where power efficiency is important. Typical applications are dc–dc converters, and power management in portable and battery powered products such as computers, printers, cellular and cordless phones. They can also be used for low voltage motor controls in mass storage products such as disk drives and tape drives.

- Ultra Low On–Resistance Provides Higher Efficiency and Extends Battery Life
- Logic Level Gate Drive – Can Be Driven by Logic ICs
- Withstand High Energy in Avalanche and Commutation Modes
- Diode Characterized for Use in Bridge Circuits
- Diode Exhibits High Speed, With Soft Recovery
- I_{DSS} Specified at Elevated Temperature
- Avalanche Energy Specified

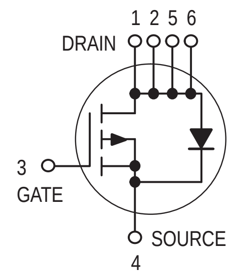
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)
Negative sign for P–Channel devices omitted for clarity

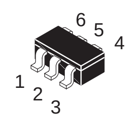
Rating	Symbol	Value	Unit
Drain–Source Voltage	V_{DSS}	20	Vdc
Drain–Gate Voltage (R_{GS} = 1.0 MΩ)	V_{DGR}	20	Vdc
Gate–Source Voltage — Continuous	V_{GS}	± 12	Vdc
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	62.5	°C/W
Total Power Dissipation Derate above 25°C	P_D	2.0 20	Watts mW/°C
Drain — Continuous — Continuous @ 70°C — Pulsed Drain Current(1)	I_D I_D I_{DM}	4.4 3.5 20	Adc
Operating and Storage Temperature Range	T_J, T_{stg}	–55 to 150	°C
Single Drain–to–Source Avalanche Energy — Starting T_J = 25°C (V_{DD} = 20 V, V_{GS} = 4.5 Vdc, I_L = 10 A, L = 1.5 mH, R_G = 25 Ω)	E_{AS}	75	mJ

(1) Repetitive rating: pulse width limited by maximum junction temperature.

ON Semiconductor
Formerly a Division of Motorola
http://onsemi.com

SINGLE TMOS POWER MOSFET 4.4 AMPERES 20 VOLTS $R_{DS(on)}$ = 0.065 Ω





TSOP 6
CASE 318G
STYLE 1

ORDERING INFORMATION

Device	Package	Shipping
NGSF3443VT1	TSOP 6	7” Reel 8mm embossed tape 3000 Tape & Reel
NGSF3443VT3	TSOP 6	13” Reel 8mm embossed tape 10000 Tape & Reel

This document contains information on a new product. Specifications and information herein are subject to change without notice.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–to–Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 250 μAdc)		$V_{(BR)DSS}$	20	—	—	Vdc
Temperature Coefficient (Positive)			—	10.9	—	mV/°C
Zero Gate Voltage Collector Current (V_{DS} = 20 Vdc, V_{GS} = 0 Vdc)		I_{DSS}	—	—	1.0	μAdc
(V_{DS} = 20 Vdc, V_{GS} = 0 Vdc, T_J =70°C)			—	—	5.0	
Gate–Body Leakage Current (V_{GS} = ±12 Vdc, V_{DS} = 0)		I_{GSS}	—	—	100	nAdc
ON CHARACTERISTICS (1)						
Gate Threshold Voltage (I_D = 250 μA, V_{DS} = V_{GS})		$V_{GS(th)}$	0.6	—	—	Vdc
Temperature Coefficient (Negative)			—	2.4	—	mV/°C
On–State Drain Current (V_{DS} = 5.0 Vdc, V_{GS} = 4.5 Vdc)		$V_{DS(on)}$	15	—	—	Adc
Static Drain–to–Source On–Resistance (V_{GS} = 4.5 Vdc, I_D = 4.4 Adc)		$R_{DS(on)}$	—	56	65	mΩ
(V_{GS} = 2.7 Vdc, I_D = 3.7 Adc)			—	73	90	
(V_{GS} = 2.5 Vdc, I_D = 3.5 Adc)			—	78	100	
Forward Transconductance (V_{DS} = 10 Vdc, I_D = 4.4 Adc)		g_{FS}	—	11	—	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 16 Vdc, V_{GS} = 0 Vdc, f = 1.0 MHz)	C_{iss}	—	485	680	pF
Output Capacitance		C_{oss}	—	190	270	
Transfer Capacitance		C_{rss}	—	70	100	
SWITCHING CHARACTERISTICS (2)						
Turn–On Delay Time	(V_{DD} = 10 Vdc, I_D = 1.0 Adc, V_{GS} = 4.5 Vdc, R_G = 6.0 Ω)	$t_{d(on)}$	—	9.2	50	ns
Rise Time		t_r	—	20.3	60	
Turn–Off Delay Time		$t_{d(off)}$	—	29.4	100	
Fall Time		t_f	—	37.3	80	
Gate Charge	(V_{DS} = 80 Vdc, I_D = 30 Adc, V_{GS} = 10 Vdc)	Q_T	—	8.1	15	nC
		Q_1	—	1.4	—	
		Q_2	—	2.6	—	
		Q_3	—	2.7	—	
SOURCE–DRAIN DIODE CHARACTERISTICS						
Forward On–Voltage	(I_S = 1.7 Adc, V_{GS} = 0 Vdc)	V_{SD}	—	0.93	1.2	Vdc
	(I_S = 1.7 Adc, V_{GS} = 0 Vdc, T_J = 125°C)		—	0.87	—	
Reverse Recovery Time	(I_S = 2.1 Adc, V_{GS} = 0 Vdc, dI_S/dt = 100 A/μs)	t_{rr}	—	27.5	80	ns
		t_a	—	11.3	—	
		t_b	—	16.2	—	
Reverse Recovery Stored Charge		Q_{RR}	—	0.0156	—	μC

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
(2) Switching characteristics are independent of operating junction temperature.

TYPICAL ELECTRICAL CHARACTERISTICS

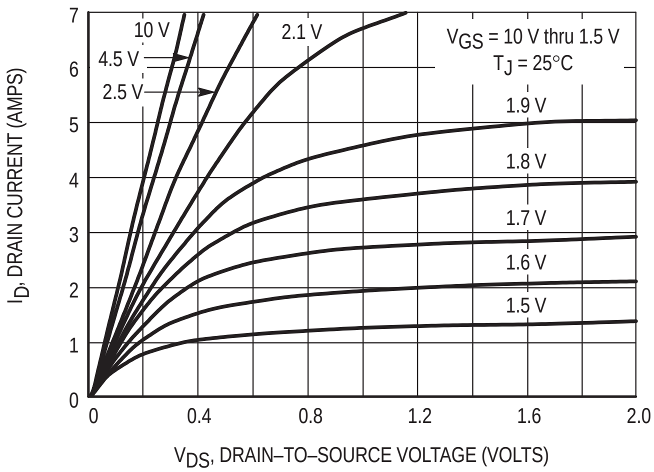


Figure 1. On–Region Characteristics

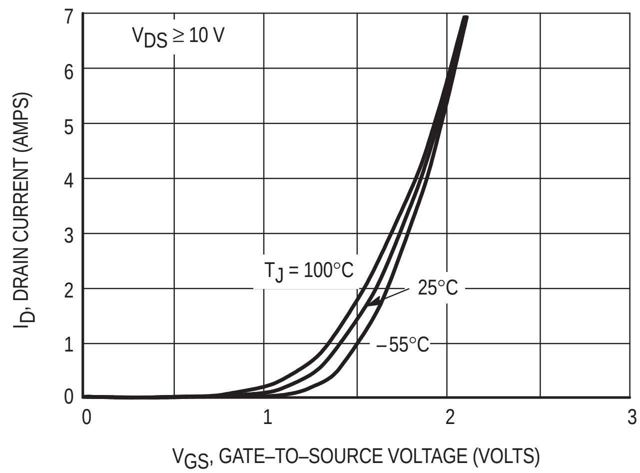


Figure 2. Transfer Characteristics

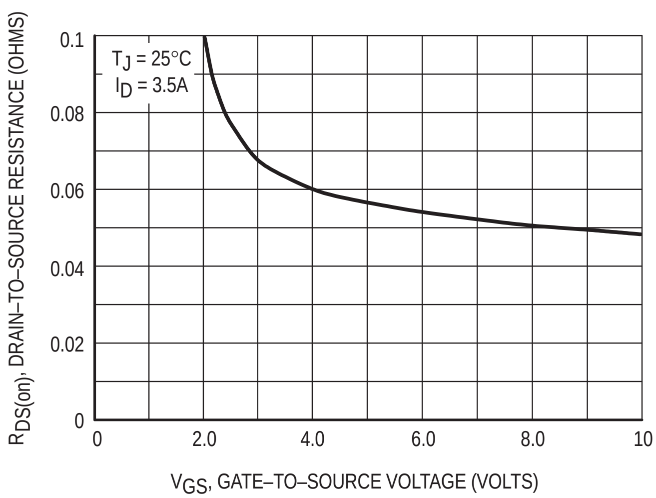


Figure 3. On–Resistance versus Gate–to–Source Voltage

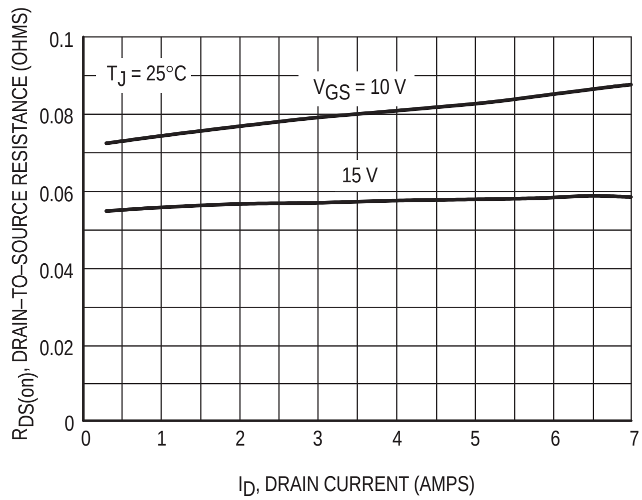


Figure 4. On–Resistance versus Drain Current and Gate Voltage

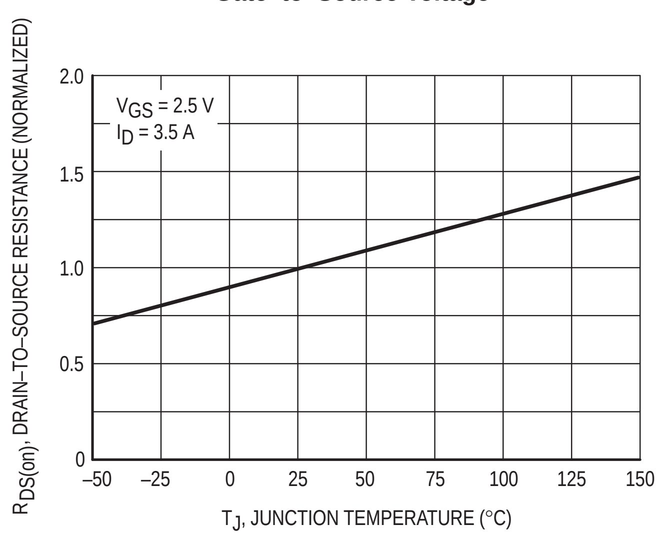


Figure 5. On–Resistance Variation with Temperature

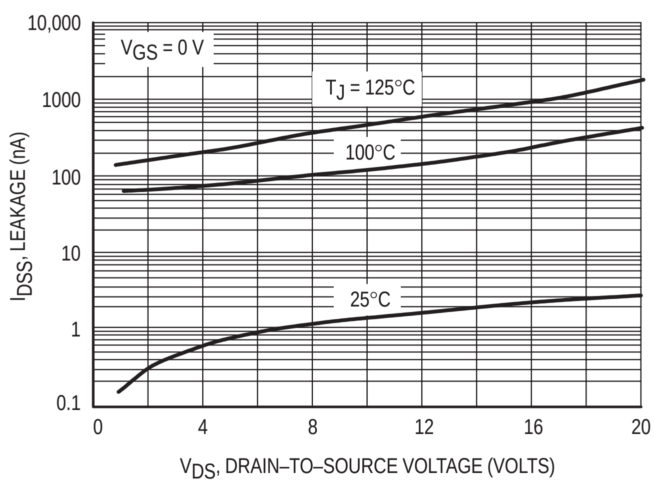


Figure 6. Drain–To–Source Leakage Current versus Voltage

POWER MOSFET SWITCHING

Switching behavior is most easily modeled and predicted by recognizing that the power MOSFET is charge controlled. The lengths of various switching intervals (Δt) are determined by how fast the FET input capacitance can be charged by current from the generator.

The published capacitance data is difficult to use for calculating rise and fall because drain–gate capacitance varies greatly with applied voltage. Accordingly, gate charge data is used. In most cases, a satisfactory estimate of average input current ($I_{G(AV)}$) can be made from a rudimentary analysis of the drive circuit so that

$t = Q/I_{G(AV)}$

During the rise and fall time interval when switching a resistive load, V_{GS} remains virtually constant at a level known as the plateau voltage, V_{SGP}. Therefore, rise and fall times may be approximated by the following:

$t_r = Q_2 \times R_G/(V_{GG} - V_{GSP})$

$t_f = Q_2 \times R_G/V_{GSP}$

where

V_{GG} = the gate drive voltage, which varies from zero to V_{GG}

R_G = the gate drive resistance

and Q_2 and V_{GSP} are read from the gate charge curve.

During the turn–on and turn–off delay times, gate current is not constant. The simplest calculation uses appropriate values from the capacitance curves in a standard equation for voltage change in an RC network. The equations are:

$t_{d(on)} = R_G\, C_{iss}\, \text{In}\, [V_{GG}/(V_{GG} - V_{GSP})]$

$t_{d(off)} = R_G\, C_{iss}\, \text{In}\, (V_{GG}/V_{GSP})$

The capacitance (C_{iss}) is read from the capacitance curve at a voltage corresponding to the off–state condition when calculating $t_{d(on)}$ and is read at a voltage corresponding to the on–state when calculating $t_{d(off)}$.

At high switching speeds, parasitic circuit elements complicate the analysis. The inductance of the MOSFET source lead, inside the package and in the circuit wiring which is common to both the drain and gate current paths, produces a voltage at the source which reduces the gate drive current. The voltage is determined by Ldi/dt, but since di/dt is a function of drain current, the mathematical solution is complex. The MOSFET output capacitance also complicates the mathematics. And finally, MOSFETs have finite internal gate resistance which effectively adds to the resistance of the driving source, but the internal resistance is difficult to measure and, consequently, is not specified.

The resistive switching time variation versus gate resistance (Figure 9) shows how typical switching performance is affected by the parasitic circuit elements. If the parasitics were not present, the slope of the curves would maintain a value of unity regardless of the switching speed. The circuit used to obtain the data is constructed to minimize common inductance in the drain and gate circuit loops and is believed readily achievable with board mounted components. Most power electronic loads are inductive; the data in the figure is taken with a resistive load, which approximates an optimally snubbed inductive load. Power MOSFETs may be safely operated into an inductive load; however, snubbing reduces switching losses.

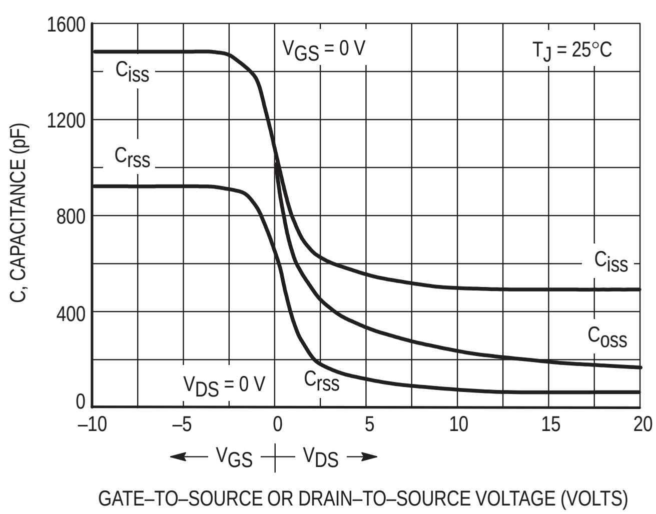


Figure 7. Capacitance Variation

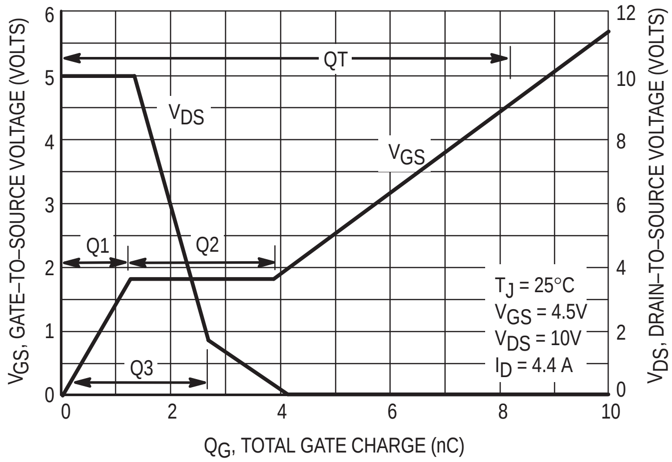


Figure 8. Gate–To–Source and Drain–To–Source Voltage versus Total Charge

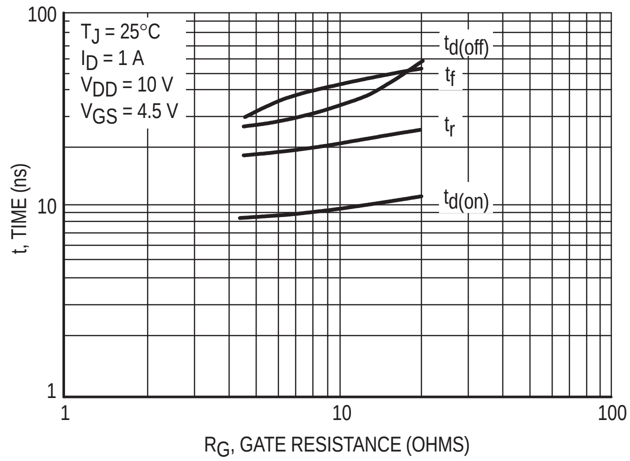


Figure 9. Resistive Switching Time Variation versus Gate Resistance

DRAIN–TO–SOURCE DIODE CHARACTERISTICS

The switching characteristics of a MOSFET body diode are very important in systems using it as a freewheeling or commutating diode. Of particular interest are the reverse recovery characteristics which play a major role in determining switching losses, radiated noise, EMI and RFI.

System switching losses are largely due to the nature of the body diode itself. The body diode is a minority carrier device, therefore it has a finite reverse recovery time, t_{rr}, due to the storage of minority carrier charge, Q_{RR}, as shown in the typical reverse recovery wave form of Figure 15. It is this stored charge that, when cleared from the diode, passes through a potential and defines an energy loss. Obviously, repeatedly forcing the diode through reverse recovery further increases switching losses. Therefore, one would like a diode with short t_{rr} and low Q_{RR} specifications to minimize these losses.

The abruptness of diode reverse recovery effects the amount of radiated noise, voltage spikes, and current ringing. The mechanisms at work are finite irremovable circuit parasitic inductances and capacitances acted upon by high di/dts. The diode's negative di/dt during t_a is directly controlled by the device clearing the stored charge. However, the positive di/dt during t_b is an uncontrollable diode characteristic and is usually the culprit that induces current ringing. Therefore, when comparing diodes, the ratio of t_b/t_a serves as a good indicator of recovery abruptness and thus gives a comparative estimate of probable noise generated. A ratio of 1 is considered ideal and values less than 0.5 are considered snappy.

Compared to ON Semiconductor standard cell density low voltage MOSFETs, high cell density MOSFET diodes are faster (shorter t_{rr}), have less stored charge and a softer reverse recovery characteristic. The softness advantage of the high cell density diode means they can be forced through reverse recovery at a higher di/dt than a standard cell MOSFET diode without increasing the current ringing or the noise generated. In addition, power dissipation incurred from switching the diode will be less due to the shorter recovery time and lower switching losses.

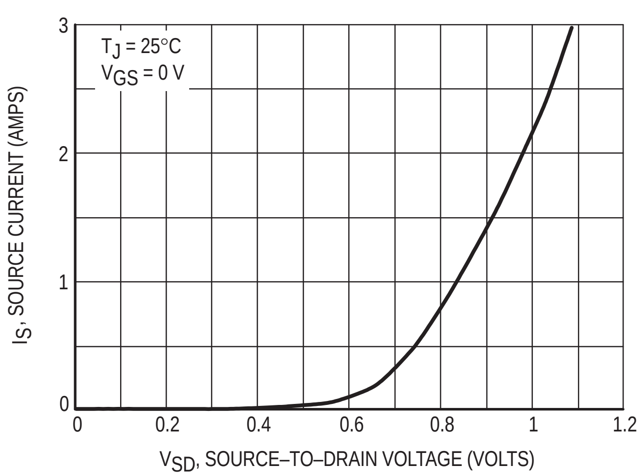


Figure 10. Diode Forward Voltage versus Current

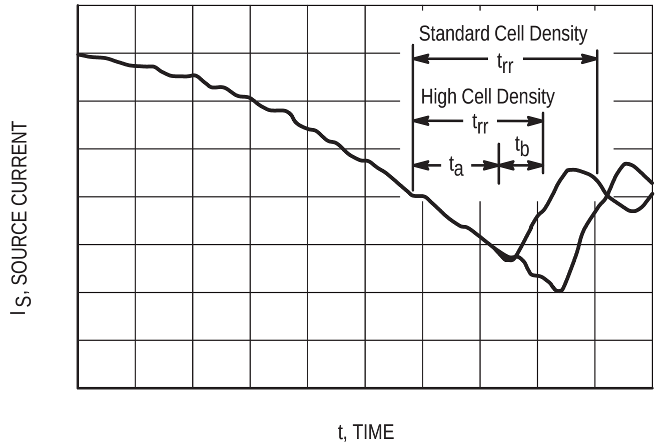


Figure 11. Reverse Recovery Time (t_{rr})

SAFE OPERATING AREA

The Forward Biased Safe Operating Area curves define the maximum simultaneous drain–to–source voltage and drain current that a transistor can handle safely when it is forward biased. Curves are based upon maximum peak junction temperature and a case temperature (T_C) of 25°C. Peak repetitive pulsed power limits are determined by using the thermal response data in conjunction with the procedures discussed in AN569, "Transient Thermal Resistance — General Data and Its Use."

Switching between the off–state and the on–state may traverse any load line provided neither rated peak current (I_{DM}) nor rated voltage (V_{DSS}) is exceeded, and that the transition time (t_r, t_f) does not exceed 10 μs. In addition the total power averaged over a complete switching cycle must not exceed $(T_{J(MAX)} - T_C)/(R_{\theta JC})$.

A power MOSFET designated E–FET can be safely used in switching circuits with unclamped inductive loads. For reliable operation, the stored energy from circuit inductance dissipated in the transistor while in avalanche must be less than the rated limit and must be adjusted for operating conditions differing from those specified. Although industry practice is to rate in terms of energy, avalanche energy capability is not a constant. The energy rating decreases non–linearly with an increase of peak current in avalanche and peak junction temperature.

Although many E–FETs can withstand the stress of drain–to–source avalanche at currents up to rated pulsed current (I_{DM}), the energy rating is specified at rated continuous current (I_D), in accordance with industry custom. The energy rating must be derated for temperature as shown in the accompanying graph (Figure 13). Maximum energy at currents below rated continuous I_D can safely be assumed to equal the values indicated.

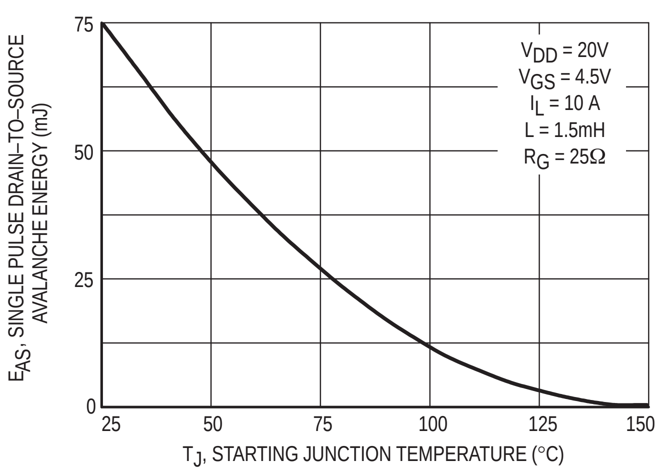


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

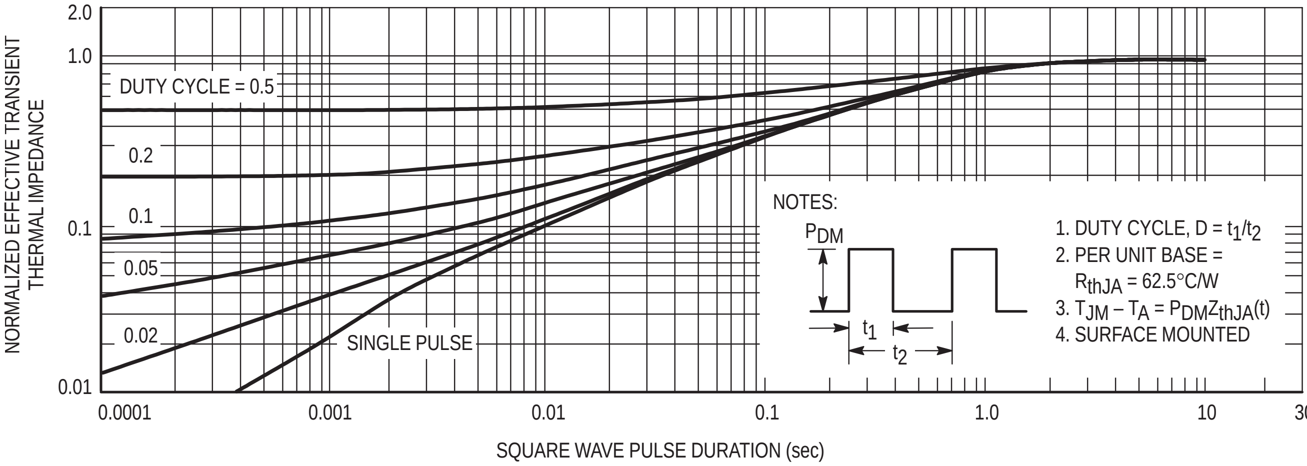


Figure 13. Thermal Response

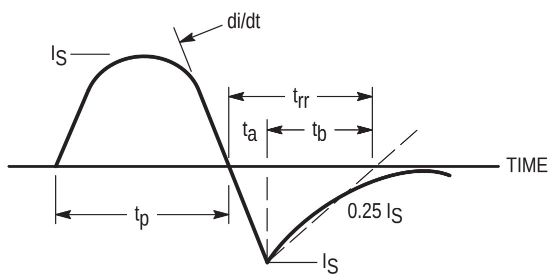
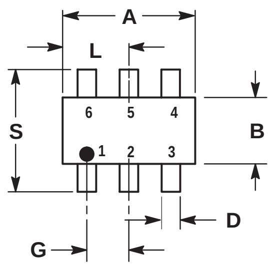


Figure 14. Diode Reverse Recovery Waveform

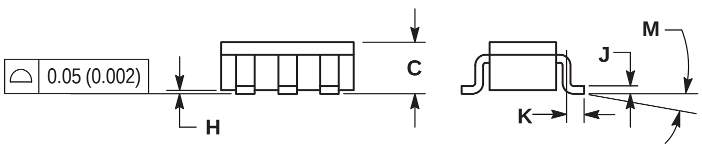
PACKAGE DIMENSIONS

TSOP 6
CASE 318G–02
ISSUE A



STYLE 1:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.1142	0.1220
B	1.30	1.70	0.0512	0.0669
C	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.05	0.0335	0.0413
H	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
M	0 °	10 °	0 °	10 °
S	2.50	3.00	0.0985	0.1181

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